

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of :
Kee-won KWON et al. : Attn: Applications Branch
Serial No. [NEW] : Attorney Docket No. SEC.1032
Filed: 8 July 2003 :
For: SEMICONDUCTOR MEMORY DEVICE WITH STRUCTURE PROVIDING
INCREASED OPERATING SPEED

PRELIMINARY AMENDMENT

Honorable Assistant Commissioner
of Patents and Trademarks,
Washington, D.C. 20231

Sir:

Preliminary to the examination of the above-identified application, please enter
the following amendments and remarks.

IN THE SPECIFICATION

Kindly amend the specification as follows:

Page 12, please replace the following paragraph with the same paragraph
number:

--[00057] Hereinafter, a comparison of the structures of the semiconductor
memory devices of FIGS. 5 and 6 will be described. The semiconductor memory
device of FIG. 5 includes the memory array blocks 31 through 38 that are each divided
into three memory sub-blocks 31a through 38a, respectively. Each memory sub-block
has a memory cell of 352 bits per word line. That is, a total of twenty-four memory sub-